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P-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
	0.0065 at V _{GS} = - 4.5 V	- 21		
- 12	0.008 at V _{GS} = - 2.5 V	- 19		
	0.011 at V _{GS} = - 1.8V	- 16		

FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET[®] Power MOSFET
- New Low Thermal Resistance PowerPAK[®] Package with Low 1.07 mm Profile



APPLICATIONS

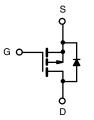
· Load Switch

PowerPAK SO-8

Bottom View

Ordering Information: Si7495DP-T1-E3 (Lead (Pb)-free)

Si7495DP-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unle	ss otherwise i	noted			
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V_{DS}	- 12		V	
Gate-Source Voltage		V_{GS}	± 8			
Continuous Drain Current /T = 150 °C\8	T _A = 25 °C	I _D	- 21	- 13		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 17	- 10	۸	
Pulsed Drain Current		I _{DM}	- 50		Α	
Continuous Source Current (Diode Conduction) ^a		I _S	- 4.5	- 1.6		
Maximum Dawar Dissination	T _A = 25 °C	P _D	5	1.8	W	
Maximum Power Dissipation ^a	T _A = 70 °C		3.2	1.1		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	
Soldering Recommendations (Peak Temperature)b, c		-	260		ı	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Marian and Luncking to Aughing to	t ≤ 10 s	- R _{thJA}	20	25	°C/W
Maximum Junction-to-Ambient ^a	Steady State		54	68	
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	1.7	2.2	

Notes

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See Solder Profile (<u>www.vishay.com/ppg?73257</u>). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

Vishay Siliconix



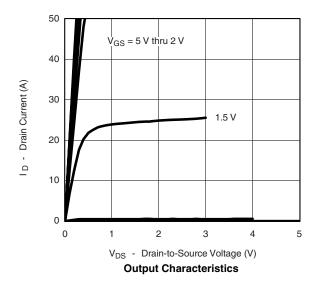
Parameter Symb		Test Conditions	Min	Тур	Max	Unit	
Static					•		
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -1$ mA	- 0.4		- 0.9	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 12 V, V _{GS} = 0 V			- 1		
		$V_{DS} = -12 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 ^{\circ}\text{C}$			-10	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le$ - 5 V, $V_{GS} =$ - 4.5 V	- 40			Α	
Drain-Source On-State Resistance ^a		$V_{GS} = -4.5 \text{ V}, I_D = -21 \text{ A}$		0.0054	0.0065	Ω	
	R _{DS(on)}	$V_{GS} = -2.5 \text{ V}, I_D = -19 \text{ A}$		0.0065	0.008		
		$V_{GS} = -1.8 \text{ V}, I_D = -16 \text{ A}$		0.0088	0.011	Ī	
Forward Transconductance ^a	g _{fs}	V _{DS} = - 15 V, I _D = - 21 A		80		S	
Diode Forward Voltage ^a	V _{SD}	$I_S = -4.5 \text{ A}, V_{GS} = 0 \text{ V}$		- 0.65	- 1.1	٧	
Dynamic ^b	<u> </u>		_				
Total Gate Charge	Qg			93	140	nC	
Gate-Source Charge	Q _{gs}	$V_{DS} = -6 \text{ V}, V_{GS} = -5 \text{ V}, I_{D} = -21 \text{ A}$		10.5			
Gate-Drain Charge				22			
Gate Resistance	R_g			2.7		Ω	
Turn-On Delay Time	t _{d(on)}			100	150		
Rise Time	t _r	V_{DD} = - 6 V, R_L = 6 Ω		200	300	ns	
Turn-Off Delay Time		$I_D\cong$ - 1 A, $V_{GEN}=$ - 4.5 V, $R_g=6~\Omega$		350	530		
Fall Time	t _f			230	350	113	
Source-Drain Reverse Recovery Time	t _{rr}	$I_F = -2.9 \text{ A}, dI/dt = 100 \text{ A/}\mu\text{s}$		110	165		

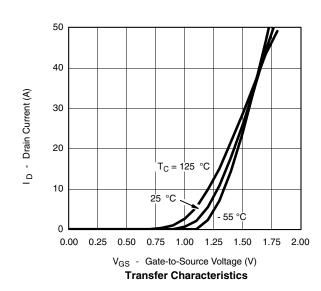
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless noted



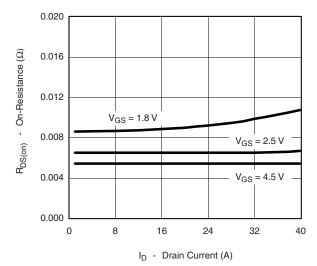




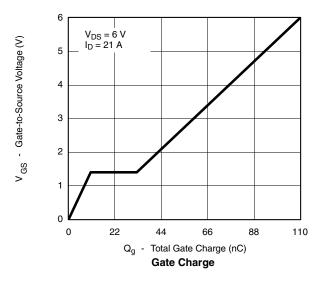


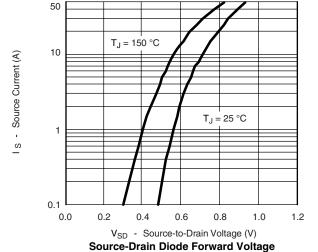


TYPICAL CHARACTERISTICS 25 °C, unless noted



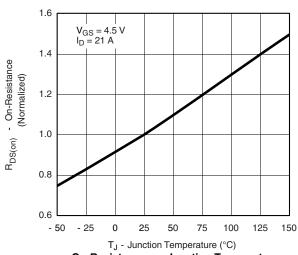
On-Resistance vs. Drain Current



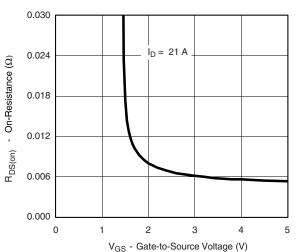


11000 C_{iss} C_{iss} C_{oss} C_{oss} 2200 C_{rss} 2200 C_{rss} 24 6 8 10 12

V_{DS} - Drain-to-Source Voltage (V) **Capacitance**



On-Resistance vs. Junction Temperature

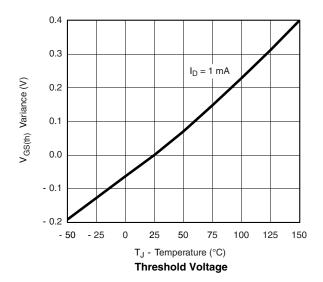


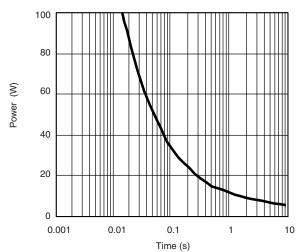
On-Resistance vs. Gate-to-Source Voltage

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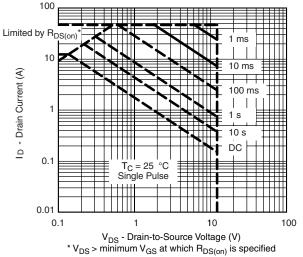
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TYPICAL CHARACTERISTICS 25 °C, unless noted

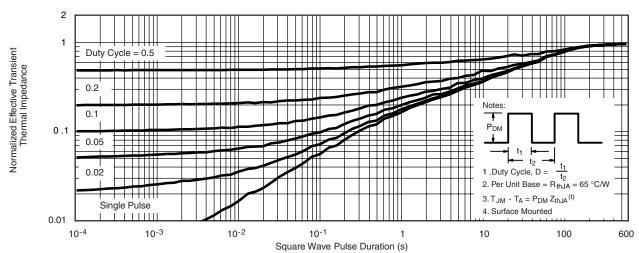




Single Pulse Power, Junction-to-Ambient



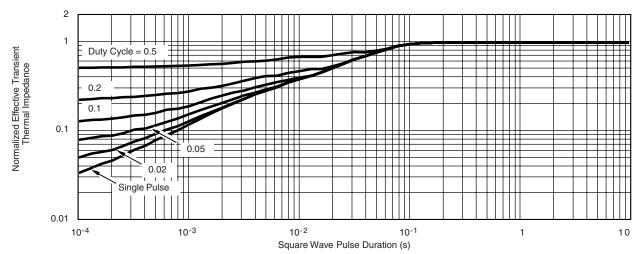
Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless noted



Normalized Thermal Transient Impedance, Junction-to-Case

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